

Silicon Power Diode

PSM/PSMR 200K
PSMF/PSMFR 200K

$I_{F(AV)} = 200 \text{ A}$
 $V_{RRM} = 100 - 1000 \text{ V}$

Preliminary Data Sheet

V_{RRM} max. repetitive peak voltage (V)	$V_{R(RMS)}$ max. RMS reverse voltage (V)	V_R max. DC blocking voltage (V)	recommended RMS working voltage (V)	Type
100	70	100	40	PSM/PSMR 200/01K
200	140	200	80	PSM/PSMR 200/02K
400	280	400	160	PSM/PSMR 200/04K
600	420	600	240	PSM/PSMR 200/06K
800	560	800	320	PSM/PSMR 200/08K
1000	700	1000	400	PSM/PSMR 200/10K

with terminal lead

PSMF/PSMFR 200/01K
PSMF/PSMFR 200/02K
PSMF/PSMFR 200/04K
PSMF/PSMFR 200/06K
PSMF/PSMFR 200/08K
PSMF/PSMFR 200/10K

Symbol	Conditions	Maximum Ratings
$I_{F(AV)}$	$T_c = 130^\circ\text{C}$	200 A
I_{FSM}	$T_{vj} = 45^\circ\text{C}$ t = 10 ms	4300 A
I_{FRM}	max. peak cycle repetitive surge current	1100 A
I^2t	max. I^2t rating (non-rep.) for 5 to 10 ms	92500 A ² s
$I_{R(AV)}$	max. average reverse leakage current at V_{RRM} ; $T_c = 25^\circ\text{C}$	min. 30 μA max. 50 μA
V_{FM}	max. peak forward voltage drop @ rated $I_{F(AV)}$	1.35 V
R_{thJC}	max. thermal resistance junction to case	0.2 K/W
T_{vj}	operating junction temperature	-65... + 150 $^\circ\text{C}$
T_{vjM}	max. virtual junction temperature	150 $^\circ\text{C}$
T_{stg}	storage temperature	-65... + 200 $^\circ\text{C}$
M_d	mounting torque (non-lubricated threads)	min. 2.0 mkg max. 3.0 mkg
Weight	typ.	150 g

Features

- Diffused Series
- Available in Normal & Reverse Polarity
- Industrial Grade
- Available in Avalanche Characteristic

